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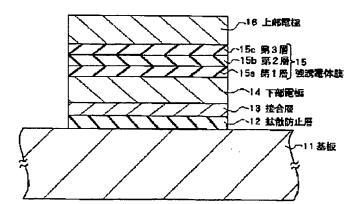
H01L 27/108 H01L 21/8242 H01L 21/8247 H01L 29/788 H01L 29/792 //

H01L 21/316

TITLE

: FERROELECTRIC CAPACITOR AND

MANUFACTURE THEREOF, AND MEMORY CELL THEREWITH



ABSTRACT: PROBLEM TO BE SOLVED: To miniaturize a device by reducing the size of crystal grains while maintaining excellent ferroelectric characteristics.

> SOLUTION: A lower electrode 14, a ferroelectric film 15 and an upper electrode are formed on a substrate 11. The ferroelectric film 15 is laminated with a plurality of layers 15a, 15b and 15c containing polycrystalline lamellar crystal structure oxide (Bi_x(Sr, Ca, Ba)_v(Ta, Nb)₂O_{0±d}) and divided each other. In this case, at least one layer of the layers 15a, 15b and 15c has different (Sr, Ca, Ba) component ratio y from other layers. In other words, (Sr, Ca, Ba) component ratio y of the ferroelectric film 15 is made to change. Thereby, the size of the crystal grains in the lamellar crystal structure oxide is reduced while excellent ferroelectric characteristics is obtained.

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